

N-channel 40 V, 3.3 mΩ standard level MOSFET in LFPAK33 29 January 2019 Product data sheet

### 1. General description

Automotive qualified standard level N-channel MOSFET in an LFPAK33 package using Trench 9 TrenchMOS technology. This product has been designed and qualified to AEC-Q101 for use in high performance automotive applications.

#### 2. Features and benefits

- Fully automotive qualified to AEC-Q101 at 175 °C
- Trench 9 superjunction technology:
- · Low power losses, high power density
- LFPAK copper clip package technology:
  - High robustness and reliability
  - Gull wing leads for high manufacturability and AOI
- Repetitive avalanche rated

### 3. Applications

- 12 V automotive systems
- · Powertrain, chassis, body and infotainment applications
- Medium/Low power motor drive
- DC-DC systems
- LED lighting

### 4. Quick reference data

Table 1. Qui	ick reference data	1					
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	-	40	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	[1]	-	-	80	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	-	101	W
Static chara	acteristics			·			
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 11		1.8	2.6	3.3	mΩ
Dynamic ch	haracteristics						
Q <sub>GD</sub>	gate-drain charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 32 V; V <sub>GS</sub> = 10 V; Fig. 13; Fig. 14		-	6.6	13.2	nC
Source-dra	in diode			·			
Q <sub>r</sub>	recovered charge			-	21	-	nC

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
S		$I_{S} = 25 \text{ A}; \text{ d}I_{S}/\text{d}t = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V}; \\ \text{V}_{DS} = 20 \text{ V}; \text{ T}_{j} = 25 ^{\circ}\text{C}; \text{ Fig. 16}$	-	0.68	-	

[1] 80A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

### 5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		D
2	S	source		
3	S	source		G-UHA)
4	G	gate		mbb076 S
mb	D	Mounting base; connected to drain	LFPAK33 (SOT1210)	

### 6. Ordering information

Table 3. Ordering information							
Type number	Package	age					
	Name	Description	Version				
BUK7M3R3-40H	LFPAK33	Plastic, single ended surface mounted package (LFPAK33); 8 leads; 0.65 mm pitch	SOT1210				

### 7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK7M3R3-40H	73H340

### 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	40	V
V <sub>GS</sub>	gate-source voltage	DC; T <sub>j</sub> ≤ 175 °C		-10	20	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	101	W
ID	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	[1]	-	80	А
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 2</u>		-	80	А
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$ ; Fig. 3		-	475	А
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drai	n diode					

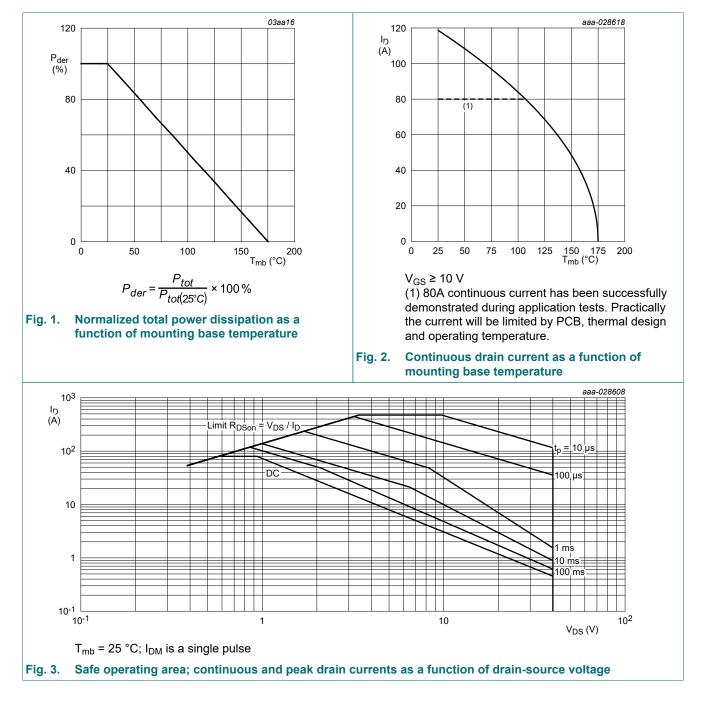
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Symbol	Parameter	Conditions		Min	Max	Unit			
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C		-	80	А			
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	475	А			
Avalanche rug	Avalanche ruggedness								
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$\label{eq:ld} \begin{array}{l} I_{D} = 80 \; A; \; V_{sup} \leq \; 40 \; V; \; R_{GS} = 50 \; \Omega; \\ V_{GS} = \; 10 \; V; \; T_{j(init)} = 25 \; ^{\circ}C; \; unclamped; \\ \hline Fig. \; \frac{4}{} \end{array}$	[2] [3]	-	57	mJ			

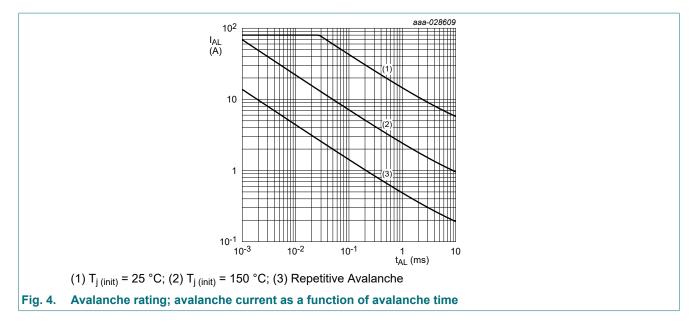
[1] 80A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

[2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

[3] Refer to application note AN10273 for further information.

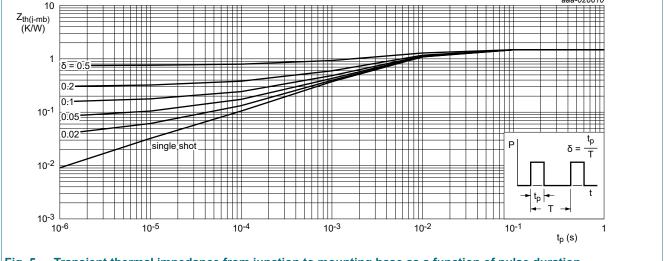


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### 9. Thermal characteristics

			Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. <u>5</u>	-	1.3	1.48	K/W



#### Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

### **10. Characteristics**

Table 7. Cha	racteristics						
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
Static characteristics							
V <sub>(BR)DSS</sub>	drain-source	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C		40	43	-	V
	breakdown voltage	$I_D$ = 250 µA; $V_{GS}$ = 0 V; $T_j$ = -40 °C		-	40.5	-	V

BUK7M3R3-40H

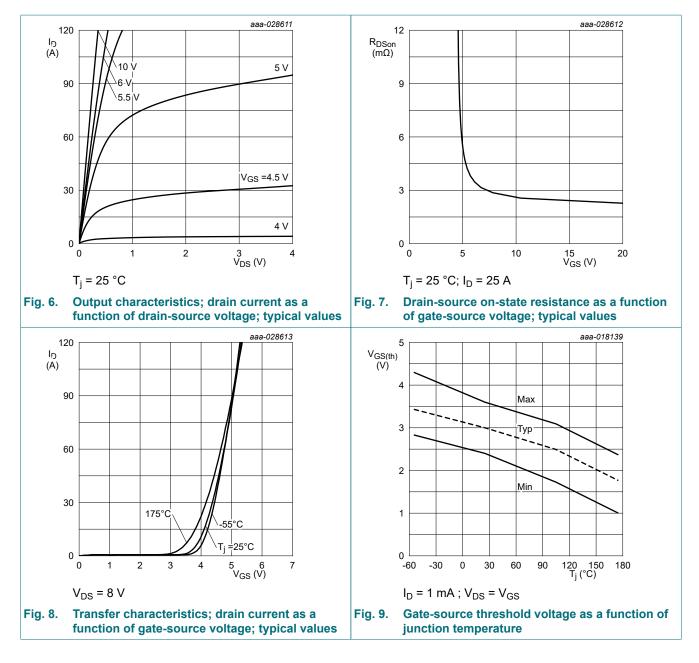
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -55 °C	36	40	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 25 \text{ °C}; Fig. 9;$ Fig. 10	2.4	3	3.6	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}; Fig. 9$	-	-	4.3	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = 175 °C; <u>Fig. 9</u>	1	-	-	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	V; T_j = -55 °C 36 40 - V   T_j = 25 °C; Fig. 9; 2.4 3 3.6 V   T_j = -55 °C; Fig. 9; 2.4 3 3.6 V   T_j = 175 °C; Fig. 9 1 - - V;   Y, T_j = 25 °C - 0.07 1 $\mu A$ Y; T_j = 25 °C - 0.94 10 $\mu A$ Y; T_j = 25 °C - 2 100 nA   Y; T_j = 25 °C - 2 100 nA   Y; T_j = 25 °C; 1.8 2.6 3.3 ms   Y; T_j = 105 °C; 2.5 4 5.3 ms   ; T_j = 175 °C; 2.8 4.4 5.8 ms   ; T_j = 175 °C; 3.5 5.5 7.2 ms   ; T_j = 175 °C; 3.5 5.5 7.2 ms   ; T_j = 175 °C; 2.8 4.4 5.8 ms   ; T_j = 175 °C; 3.5 5.5 7.2 ms   ; V_GS = 10 V; - 32 45 nC  - 113 250 </td <td>μA</td>	μA		
		V <sub>DS</sub> = 16 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 125 °C	-	0.94	10	μA
		V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	80	500	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
		V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; <u>Fig. 11</u>	1.8	2.6	3.3	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 105 °C; <u>Fig. 12</u>	2.5	4	5.3	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 125 °C; Fig. 12	2.8	4.4	5.8	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; <u>Fig. 12</u>	3.5	5.5	7.2	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz; T <sub>j</sub> = 25 °C	0.3	0.8	2	Ω
Dynamic ch	naracteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 10 \text{ V};$ Fig. 13; Fig. 14	-	32	45	nC
Q <sub>GS</sub>	gate-source charge		-	9	14	nC
Q <sub>GD</sub>	gate-drain charge		-	6.6	13.2	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 25 V; V <sub>GS</sub> = 0 V; f = 1 MHz;	-	2169	3037	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 15</u>	-	592	829	pF
C <sub>rss</sub>	reverse transfer capacitance		-	113	250	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 30 V; R <sub>L</sub> = 1.2 Ω; V <sub>GS</sub> = 10 V;	-	8.4	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5 \Omega$	-	7.3	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	19	-	ns
t <sub>f</sub>	fall time		-	9.1	-	ns
Source-dra	in diode	· · · · · ·				
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 25 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; <u>Fig. 16</u>	-	0.82	1.2	V
t <sub>rr</sub>	reverse recovery time	$    I_{\rm S} = 25 \; \text{A}; \; \text{dI}_{\rm S}/\text{dt} = -100 \; \text{A}/\mu\text{s}; \; \text{V}_{\rm GS} = 0 \; \text{V}; \\ \text{V}_{\rm DS} = 20 \; \text{V}    $	-	27	-	ns
Qr	recovered charge	$I_{S} = 25 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V}; \\ \text{V}_{DS} = 20 \text{ V}; \text{ Fig. 17}$	-	21	-	nC
S	softness factor	$    I_{S} = 25 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V}; \\ \text{V}_{DS} = 20 \text{ V}; \text{ T}_{j} = 25 ^{\circ}\text{C}; \text{ Fig. 16} $	-	0.68	-	
		$I_{S} = 25 \text{ A}; \text{ dI}_{S}/\text{dt} = -500 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$ $V_{DS} = 20 \text{ V}; \text{ T}_{i} = 25 ^{\circ}\text{C}; \text{ Fig. 16}$	-	0.49	-	

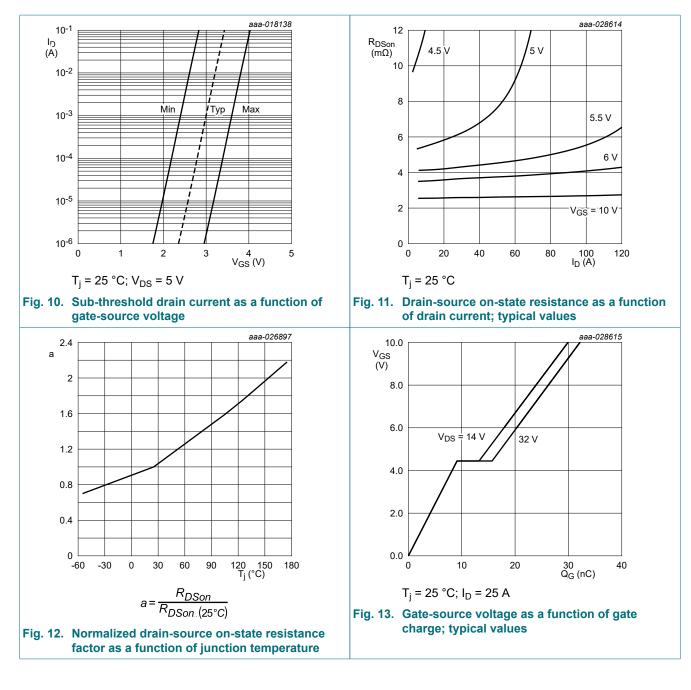
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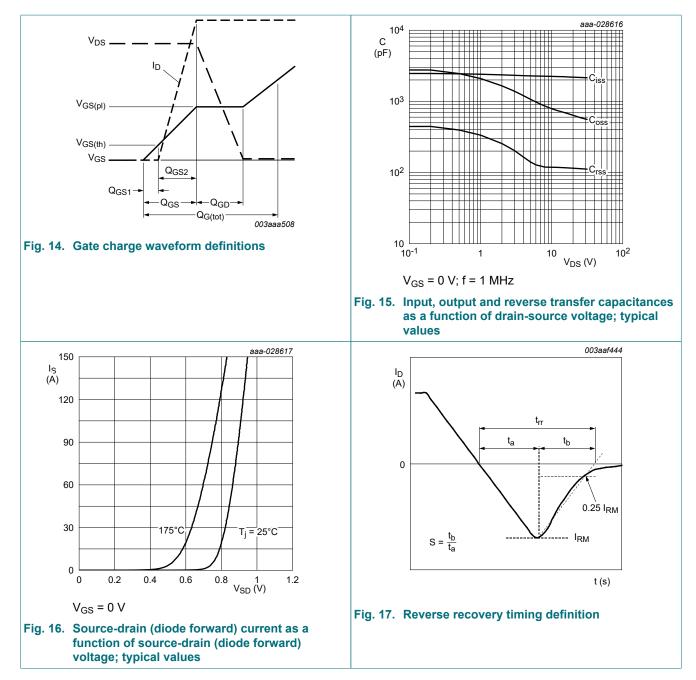
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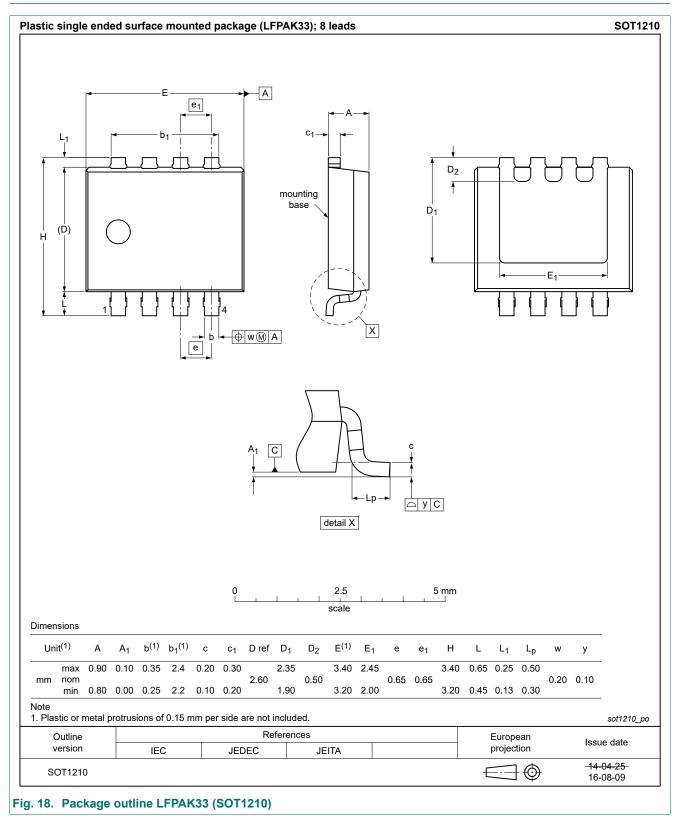
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#### N-channel 40 V, 3.3 m $\Omega$ standard level MOSFET in LFPAK33

### 11. Package outline



#### N-channel 40 V, 3.3 mΩ standard level MOSFET in LFPAK33

### 12. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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